

Docket No.: 21302/0204309-US0  
(PATENT)

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

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In re Patent Application of:  
Euijoon Yoon et al.

Application No.: 10/596,126

Confirmation No.: 2554

Filed: May 31, 2006

Art Unit: 2813

For: GROWTH METHOD OF NITRIDE  
SEMICONDUCTOR LAYER AND LIGHT  
EMITTING DEVICE USING THE GROWTH  
METHOD

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Examiner: Crawford, L. N.

**RESPONSE TO FINAL OFFICE ACTION (37 C.F.R. § 1.116)**

MS AF  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

**INTRODUCTORY COMMENTS**

In response to the Final Office Action dated June 23, 2008, and with the Examiner's approval, please amend the above-identified U.S. patent application as follows:

**Amendments to the Claims** are reflected in the listing of claims which begins on page 6 of this paper.

**Remarks/Arguments** begin on page 7 of this paper.